P-Channel 15-V (D-S) MOSFET

Top View

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PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)			
-15	0.0033 at V_{GS} = - 4.5 V	- 90	125 nC			
	0.0041 at V _{GS} = - 2.5 V	- 70	120110			

FEATURES

- DT-Trench Power MOSFET
- 100 % R_q and UIS tested

APPLICATIONS

Notebook

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- Load Switch

P-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 15	V	
Gate-Source Voltage		V _{GS}	± 8	v	
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 °C$ $T_{C} = 70 °C$ $T_{A} = 25 °C$ $T_{A} = 70 °C$	I _D	- 90 ^a -70 ^a - 26 ^{b, c} - 19 ^{b, c}		
Pulsed Drain Current		I _{DM}	-180	— A	
Continuous Source-Drain Diode Current	T _C = 25 °C T _A = 25 °C	I _S	- 90 ^a - 46 ^{b, c}	_	
Single Pulse Avalanche Current L = 0.1 mH		I _{AS}	- 40	7	
Single Pulse Avalanche Energy	L = 0.1 IIIH	E _{AS}	100	mJ	
Maximum Power Dissipation	$T_{C} = 25 \text{ °C}$ $T_{C} = 70 \text{ °C}$ $T_{A} = 25 \text{ °C}$ $T_{A} = 70 \text{ °C}$	P _D	105 67.2 6.95 ^{b, c} 4.45 ^{b, c}	w	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		-	260		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	18	25	°C/W		
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.1	1.5	0/10		

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

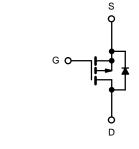
d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed

copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 54 °C/W.

DFN5X6 Top View **Bottom View** - PIN1



RoHS COMPLIANT

Din-Tek SEMICONDUCTOR

DTQ6203-D www.din-tek.jp

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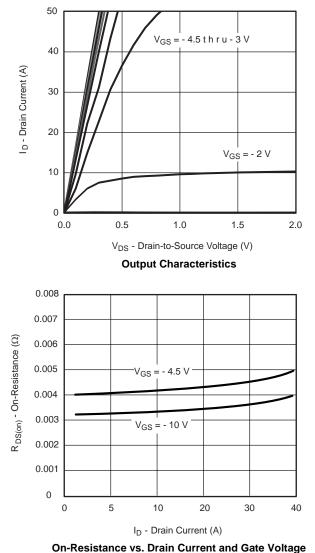
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$	- 15			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 31		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		6.5		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.3		- 1.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA
		V _{DS} = -15 V, V _{GS} = 0 V			- 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 90			А
		V _{GS} = - 4.5 V, I _D = - 20 A		0.0033	0.004	- Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 15 A		0.0041	0.005	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 8 V, I _D = - 20 A		96		S
Dynamic ^b						
Input Capacitance	C _{iss}			27050		
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		3936		pF
Reverse Transfer Capacitance	C _{rss}			1076		
Total Gate Charge	Qg	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 20 A		273	410	nC
				125	190	
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 2.5 V, I_{D} = - 15 A		39		
Gate-Drain Charge	Q _{gd}			57		
Gate Resistance	Rg	f = 1 MHz		2.9		Ω
Turn-On Delay Time	t _{d(on)}			29	30	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 15 Ω		16	30	- ns
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 10 A, V_{GEN} = - 2.5 V, R_g = 1 Ω		110	170	
Fall Time	t _f			30	50	
Turn-On Delay Time	t _{d(on)}			110	170	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 15 Ω		103	150	
Turn-Off Delay Time	t _{d(off)}	$\rm I_D\cong$ - 10 A, $\rm V_{GEN}$ = - 4.5 V, $\rm R_g$ = 1 Ω		90	150	
Fall Time	t _f			50	75	
Drain-Source Body Diode Characteristic	cs			<u> </u>	<u> </u>	
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			90	
Pulse Diode Forward Current ^a	I _{SM}				180	A
Body Diode Voltage	V _{SD}	I _S = - 5 A		- 0.70	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}			50	100	ns
Body Diode Reverse Recovery Charge	Q _{rr}			60	133	nC
Reverse Recovery Fall Time	ta	I _F = - 10 A, dl/dt = 100 A/μs, T _J = 25 °C		25		
Reverse Recovery Rise Time	t _b			24		ns

Notes:

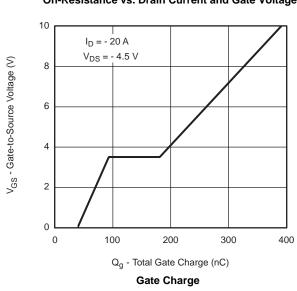
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

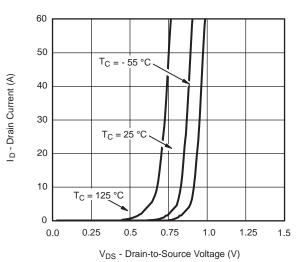
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





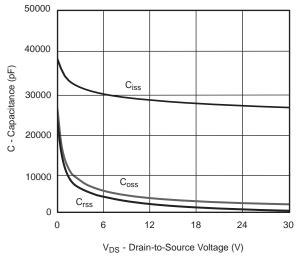
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



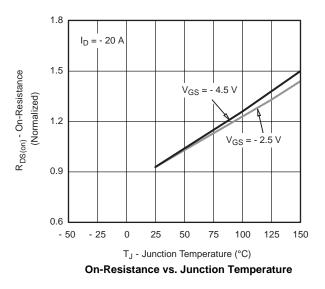


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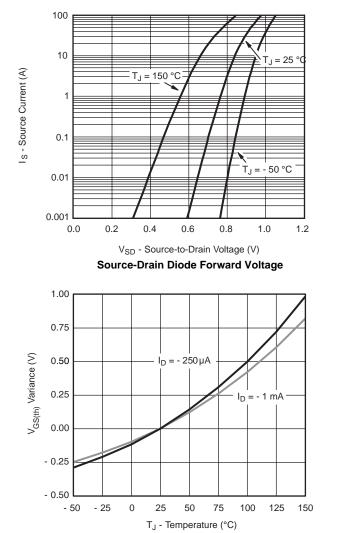
Transfer Characteristics



Capacitance

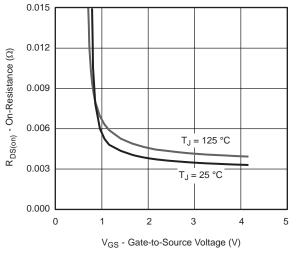




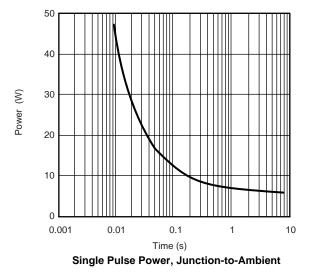


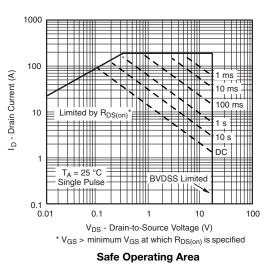
Threshold Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Gate-to-Source Voltage

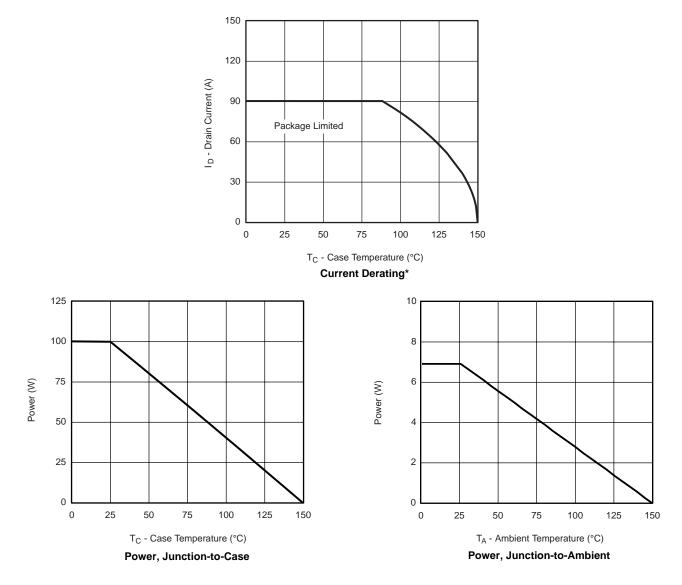






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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

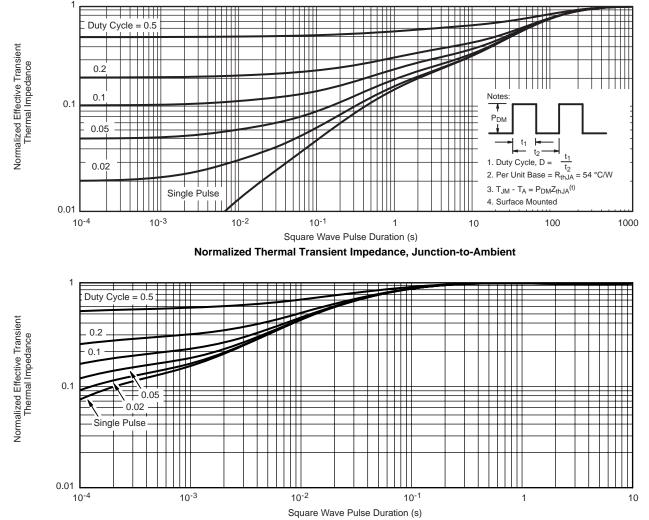


* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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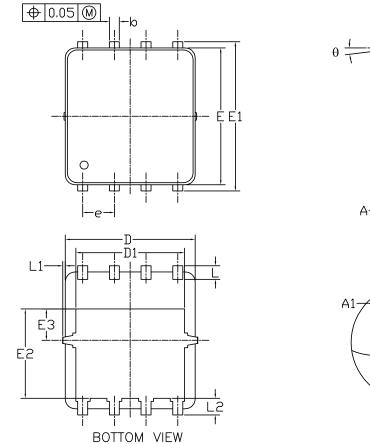


Normalized Thermal Transient Impedance, Junction-to-Case

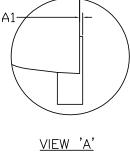
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VIEW 'A'

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DFN5x6_8L_EP1_P PACKAGE OUTLIN



(SCALE 5:1)

RECOMMENDED LAND PATTERN .60 -0.55 0.50 -0.77 -0.635 4.12 6.15 -1.60 + $\left|+\right|$ + 0.65 +t -11.27-0.50-

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SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
Al	0.00		0.05	0.000		0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
с	0.15	0.20	0.25	0.006	0.008	0.010
D	4.80	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
Е	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0		0.15	0		0.006
L2	0.68 REF			0.027 REF		
θ	0°		10°	0°		10°

UNIT: mm

NOTE 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH. 2. CONTROLLING DIMENSION IS MILLIMETER.

CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



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